

ON Semiconductor®

KSH122 / KSH122I NPN Silicon Darlington Transistor

Features

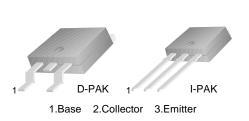
- D-PAK for Surface Mount Applications
- · High DC Current Gain
- Built-in Damper Diode at E-C
- · Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)
- Electrically Similar to Popular TIP122
- Complement to KSH127

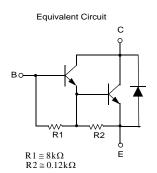
Applications

- · Switching Regulators
- Converters
- Power Amplifiers

Description

Designed for general-purpose power and switching, such as output or driver stages in applications.





Ordering Information

Part Number	Top Mark	Package	Packing Method
KSH122TF	KSH122	TO-252 3L (DPAK)	Tape and Reel
KSH122TM	KSH122	TO-252 3L (DPAK)	Tape and Reel
KSH122ITU	KSH122-I	TO-251 3L (IPAK)	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	100	V	
V _{CEO}	Collector-Emitter Voltage	100	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current (DC)	8	Α	
I _{CP}	Collector Current (Pulse)	16	Α	
I _B	Base Current	120	mA	
P _C	Collector Dissipation (T _C =25°C)	20.00	W	
	Collector Dissipation (T _A =25°C)	1.75		
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 to 150	°C	

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage ⁽¹⁾	I _C = 30 mA, I _B = 0	100			V
I _{CEO}	Collector Cut-Off Current	$V_{CE} = 50 \text{ V}, I_{B} = 0$			10	μΑ
I _{CBO}	Collector Cut-Off Current	V _{CB} = 100 V, I _E = 0			10	μΑ
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 \text{ V}, I_{C} = 0$			2	mA
h _{FE}	DC Current Gain ⁽¹⁾	$V_{CE} = 4 \text{ V}, I_{C} = 4 \text{ A}$	1000		12000	
		$V_{CE} = 4 \text{ V}, I_{C} = 8 \text{ A}$	100			
V _{CE} (sat)	Collector-Emitter Saturation Voltage ⁽¹⁾	I _C = 4 A, I _B = 16 mA			2	V
		$I_C = 8 \text{ A}, I_B = 80 \text{ mA}$			4	v
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽¹⁾	$I_C = 8 \text{ A}, I_B = 80 \text{ mA}$			4.5	V
V _{BE} (on)	Base-Emitter On Voltage ⁽¹⁾	$V_{CE} = 4 \text{ V}, I_{C} = 4 \text{ A}$			2.8	V
C _{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 0.1 \text{ MHz}$			200	pF

Note:

1. Pulse test: $pw \le 300 \mu s$, duty cycle $\le 2\%$.

Typical Performance Characteristics

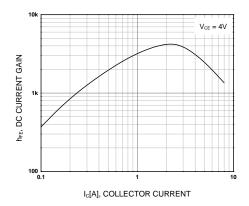


Figure 1. DC Current Gain

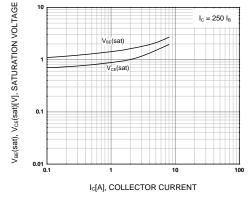


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

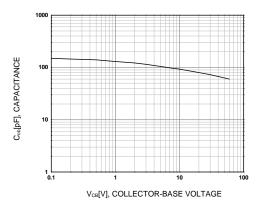


Figure 3. Collector Output Capacitance

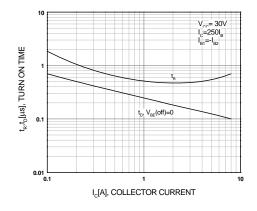


Figure 4. Turn-On Time

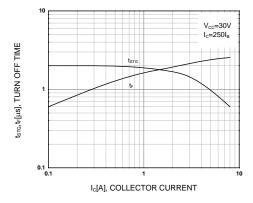


Figure 5. Turn-Off Time

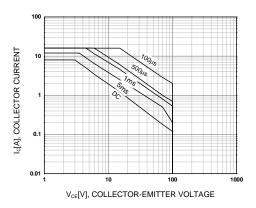


Figure 6. Safe Operating Area

Typical Performance Characteristics (Continued)

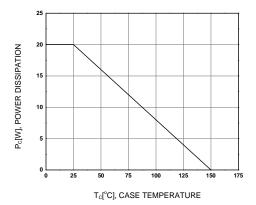


Figure 7. Power Derating

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